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Rev. 1.1, Feb. 2024

KLMCG1RCTE

eMMC Device

153FBGA, 11.5x13
64GB eMMC5.1

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	1. Updated Pin Configuration and Package Dimension.			
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	3. Updated AC Timing Parameter.			
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1.0 INTRODUCTION

1.1 General Description

SAMSUNG eMMC is an embedded MMC solution designed in a BGA package form. eMMC operation is identical to a MMC device and therefore is a simple read and write to memory using MMC protocol v5.1 which is a industry standard.

The eMMC consists of NAND flash and a MMC controller. The NAND region (V_{CC}) requires a 3V supply voltage and the MMC controller requires a 1.8V supply voltage (V_{CCQ}).
SAMSUNG eMMC supports HS400 in order to improve sequential bandwidth, especially sequential read performance.

There are several advantages of using eMMC. It is easy to use as the MMC interface allows easy integration with any microprocessor with MMC host. Any revision or amendment of NAND is invisible to the host as the embedded MMC controller insulates NAND technology from the host.
This leads to faster product development as well as faster times to market.

The embedded flash management software or FTL(Flash Transition Layer) of eMMC manages Wear Leveling, Bad Block Management and ECC.
The FTL supports all features of the Samsung NAND flash and achieves optimal performance.

1.2 Product Line-Up

[Table 1] Product Line-Up

Density	Product ID	User Density (%)	Package Size	Pin Configuration
64GB	KLMCG1RCTE-B041	91.0	11.5mm x 13mm x 0.8mm	153FBGA

1.3 General Features

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- embedded MultiMediaCard Ver. 5.1 compatible.
- SAMSUNG eMMC supports features of eMMC5.1 which are defined in JEDEC Standard.
  - Major Supported Features: HS400, Field Firmware Update, Cache, Command Queuing, Enhanced Strobe Mode, Secure Write Protection, Partition types.
  - Non-supported Features: Large Sector Size (4KB).
- Backward compatibility with previous MultiMediaCard system specification (1bit data bus, multi-eMMC systems).
- Data bus width: 1bit (Default), 4bit and 8bit.
- MMC I/F Clock Frequency: 0 ~ 200MHz
  MMC I/F Boot Frequency: 0 ~ 52MHz
- Temperature: Operation (-25°C ~ 85°C), Storage without operation (-40°C ~ 85°C)
- Power: Memory Power → V_{CC} (2.7V ~ 3.6V), Interface Power → V_{CCQ} (1.70V ~ 1.95V)

2.0 PRODUCT SPECIFICATION

2.1 Pin Description

[Table 2] Pin Description

Name	Type	Description
CLK	Input	Clock
Data Strobe	Output Push-Pull	Data Strobe is generated from eMMC to host. In HS400 mode, read data and CRC response are synchronized with Data Strobe.
CMD	Input Output Push-Pull Open-Drain	A bidirectional signal used for device initialization and command transfers. Command operates in two modes, open-drain for initialization and push-pull for fast command transfer.
DAT0-7	Input Output Push-Pull	Bidirectional data channels. It operates in push-pull mode.
RST_n	Input	H/W reset signal pin.
VDDi	Input	Internal power node to stabilize regulator output to controller core logics.
V_{CC}	Supply	Supply voltage for flash memory.
V_{CCQ}	Supply	Supply voltage for memory controller.
VSS	Supply	Ground for flash memory.
NC	-	Not Connected. NC pins can be connected to ground or left floating.
RFU	-	Reserved for Future Use. RFU pins must be left floating.
VSF	-	Vendor Specific Function. VSF pins must be left floating. Each device vendor may use these pins during device manufacturing.

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2.2 Pin Configuration

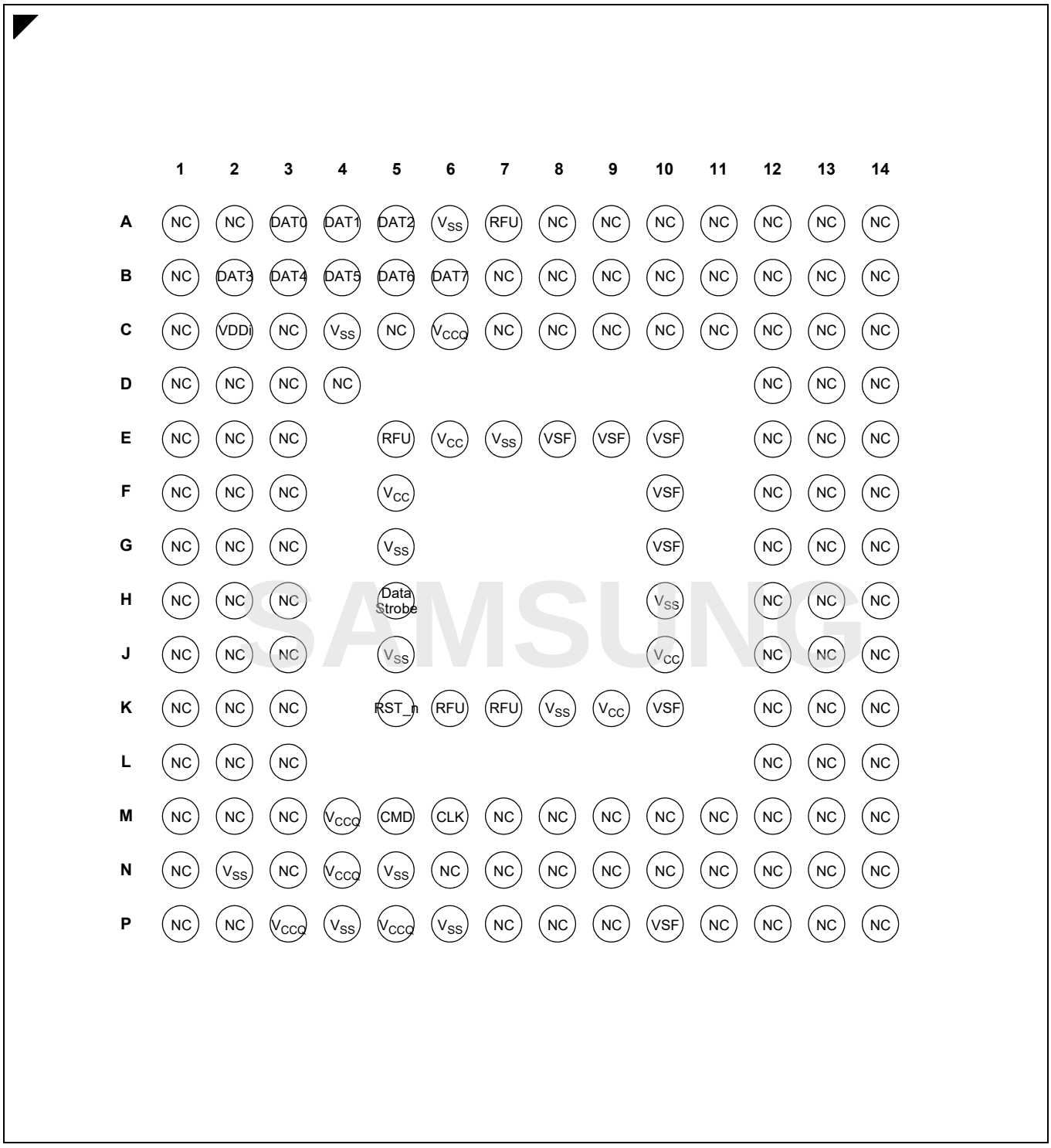


Figure 1. 153-FBGA Pin Assignment

2.3 Package Dimension

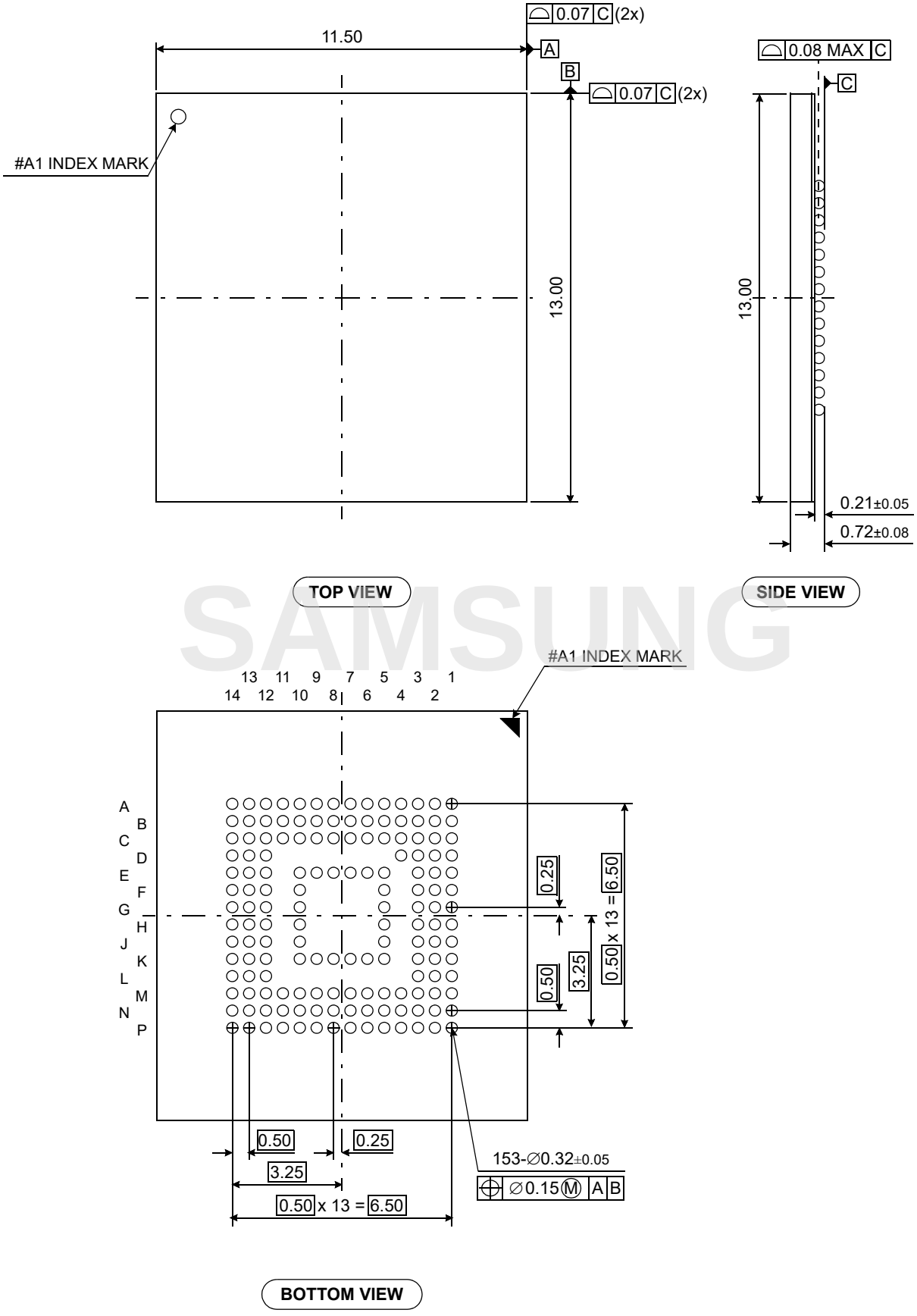


Figure 2. 11.5mm x 13mm x 0.8mm Package Dimension

IF THERE IS ANY OTHER OPERATION TO IMPLEMENT IN ADDITION TO SPECIFICATION IN THE DATASHEET OR JEDEC STANDARD, PLEASE CONTACT EACH BRANCH OFFICE OR HEADQUARTERS OF SAMSUNG ELECTRONICS.

2.4 Product Architecture

eMMC consists of NAND Flash and Controller. V_{CCQ} is for Controller power and V_{CC} is for NAND Flash power.

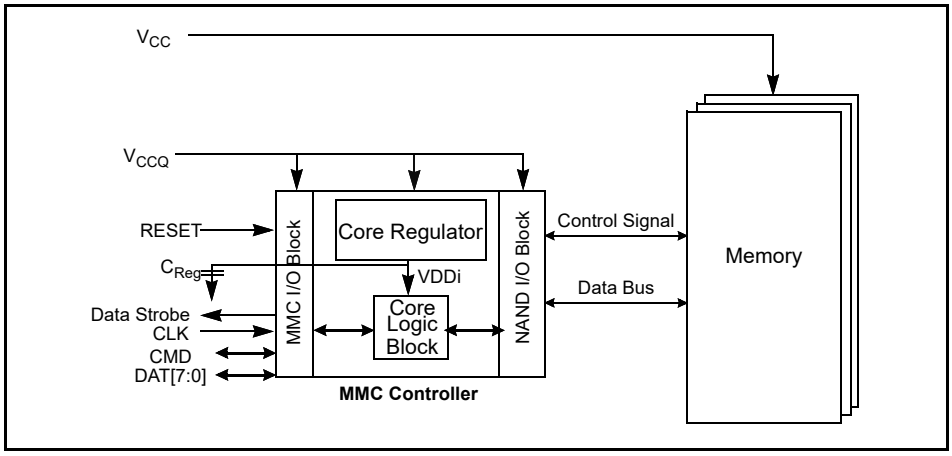


Figure 3. eMMC Block Diagram

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2.5 Power Supply

[Table 3] Power Supply Parameters

Parameter	Symbol	Min	Max	Unit
V_{CC} Supply Voltage	V_{CC}	2.7	3.6	V
V_{CCQ} Supply Voltage	V_{CCQ}	1.70	1.95	V
V_{SS} Supply Voltage	V_{SS}	-0.5	0.5	V
Supply Voltage Power Up Timing for 3.3V	tPRUH	-	35	ms
Supply Voltage Power Up Timing for 1.8V	tPRUL	-	25	ms

2.6 Temperature

[Table 4] Temperature Condition

Condition	Min	Max	Unit
Operating Temperature[1)]	-25	85	°C
Storage Temperature[2)]	-40	85	°C

NOTE :
Please refer to the qualification report for reliability testing results (available upon request).
1) Operating Temperature is the package case surface temperature of the eMMC device when eMMC device is operating.
2) Storage Temperature is the package case surface temperature of the eMMC device when power is not supplied.

2.7 Power Mode

2.7.1 Auto Power Saving Mode

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If host does not issue any command during a certain duration (1 ms), after previously issued command is completed, the device enters "Power Saving mode" to reduce power consumption automatically.

At this time, commands arriving at the device while it is in power saving mode will be serviced in normal fashion.

[Table 5] Auto Power Saving Mode and Exit Condition

Mode	Enter Condition to Auto Power Saving Mode	Exit Condition from Auto Power Saving Mode
Auto Power Saving Mode	When previous operation which came from Host is completed and no command is issued during a certain time.	If Host issues any command

[Table 6] Comparison between Auto Power Saving Mode and Sleep Mode

Mode	Auto Power Saving Mode	Sleep Mode[1)]
V_{CC} Power	ON	OFF
Time to Enter each Mode	< 1 ms	< 1 ms

NOTE :
1) To enter sleep mode, host should issue CMD5. Then V_{CC} shall be off during sleep mode. Host should send CMD5 to wake up the eMMC device from sleep mode. For more details about CMD5, refer to eMMC5.1 JEDEC standard section 6.6.21.

2.8 Performance

[Table 7] Performance

Density	Sequential Read	Sequential Write		Unit
		With SLC Buffer	Without SLC Buffer	
64GB	300	220	50	MB/s

NOTE :
Test Condition: Bus width x8, HS400, 512KB data transfer, w/o file system overhead, measured on Samsung's internal board.

3.0 HS400 MODE

eMMC 5.1 product supports high speed DDR interface timing mode up to 400MB/s at 200MHz with 1.8V I/O supply.

HS400 mode supports the following features:

- DDR Data sampling method
- CLK frequency up to 200MHz DDR (up to 400Mbps)
- Only 8-bits bus width available
- Signaling levels of 1.8V
- Five selectable Drive Strength (refer to the table below)

[Table 8] I/O Driver Strength Types

Driver Type Values	HS200 & HS400 Support	Nominal Impedance	Approximated Driving Capability Compared to Type-0	Remark
0	Mandatory	50Ω	x1	Default Driver Type. Supports up to 200MHz operation.
1	Optional	33Ω	x1.5	Supports up to 200MHz Operation.
2	Optional	66Ω	x0.75	The weakest driver that supports up to 200MHz operation.
3	Optional	100Ω	x0.5	For low noise and low EMI systems. Maximal operating frequency is decided by Host design.
4	Optional	40Ω	x1.2	Supports up to 200MHz DDR operation.

NOTE :
Support of Driver Type-0 is default for HS200 & HS400 Device, while supporting Driver types 1~ 4 are optional for HS200 & HS400 Device.

[Table 9] Device Types (EXT_CSD Register : DEVICE_TYPE [196])

Bit	Device Type	Support
7	HS400 Dual Data Rate eMMC @ 200 MHz - 1.2V I/O	No
6	HS400 Dual Data Rate eMMC @ 200 MHz - 1.8V I/O	Yes
5	HS200 Single Data Rate eMMC @ 200 MHz - 1.2V I/O	No
4	HS200 Single Data Rate eMMC @ 200 MHz - 1.8V I/O	Yes
3	High-Speed Dual Data Rate eMMC @ 52MHz - 1.2V I/O	No
2	High-Speed Dual Data Rate eMMC @ 52MHz - 1.8V or 3V I/O	Yes[1)]
1	High-Speed eMMC @ 52MHz - at rated device voltage(s)	Yes
0	High-Speed eMMC @ 26MHz - at rated device voltage(s)	Yes

NOTE :
1) Only 1.8V Supported.

[Table 10] Extended CSD Revisions (EXT_CSD Register : EXT_CSD_REV [192])

EXT_CSD_REV	Extended CSD Revision	Value
255-8	Reserved	
8	Revision 1.8 (for MMC V5.1)	0x08
7	Revision 1.7 (for MMC V5.0)	
6	Revision 1.6 (for MMC V4.5, V4.51)	
5	Revision 1.5 (for MMC V4.41)	
4	Revision 1.4 (Obsolete)	
3	Revision 1.3 (for MMC V4.3)	
2	Revision 1.2 (for MMC V4.2)	
1	Revision 1.1 (for MMC V4.1)	
0	Revision 1.0 (for MMC V4.0)	

[Table 11] High Speed Timing Interface Values (EXT_CSD Register : HS_TIMING [185])

Value	Timing Interface	Support
0x0	Selecting backwards compatibility interface timing	Yes
0x1	High Speed	Yes
0x2	HS200	Yes
0x3	HS400	Yes

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4.0 NEW eMMC 5.1 FEATURES

4.1 Overview

[Table 12] New Features List for Device Types

Function	JEDEC Standard	Support
Cache Flushing Report	Mandatory	Yes
Background operation control	Mandatory	Yes
Command Queuing	Optional	Yes
Enhanced Strobe	Optional	Yes
Cache Barrier	Optional	Yes
RPMB Throughput improve	Optional	Yes
Secure Write Protection	Optional	Yes

4.2 Command Queuing

To facilitate command queuing in eMMC, the device manages an internal task queue that the host can queue during data transfer tasks.

Every task is issued by the host and initially queued as pending. The device works to prepare pending tasks for execution. When a task is ready for execution, its state changes to “ready for execution”.

The host tracks the state of all queued tasks and may order the execution of any task, marked as “ready for execution”, by sending a command indicating its Task ID. The device executes the data transfer transaction after receiving the execute command (CMD46/CMD47).

4.2.1 Command Set Description

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[Table 13] Command Queue

CMD	Type	Argument	Resp	Abbreviation	Command Description
CMD44	ac	[31] Reliable Write Request [30] DAT_DIR - "0" write / "1" read [29] tag request [28:25] context ID [24] forced programming [23] Priority: “0” simple / “1” high [20:16] Task ID [15:0] number of blocks	R1	QUEUED_TASK _PARAMS	Define direction of operation (Read or Write) and Set high priority CMD Queue with Task ID.
CMD45	ac	[31:0] Start block address	R1	QUEUED_TASK_ADDRESS	Indicate data address for Queued CMD.
CMD46	adtc	[20:16] Task ID	R1	EXECUTE_READ_TASK	(Read) Transmit the requested number of data blocks.
CMD47	adtc	[20:16] Task ID	R1	EXECUTE_WRITE_TASK	(Write) Transmit the requested number of data blocks.
CMD48	ac	[20:16] Task ID [3:0] TM op-code	R1b	CMDQ_TASK _MGMT	Reset a specific task or entire queue. [20:16] when TM op-code = 2h these bits represent Task ID. When TM op-code = 1h these bits are reserved.

4.2.2 New Response : QSR (Queue Status Register)

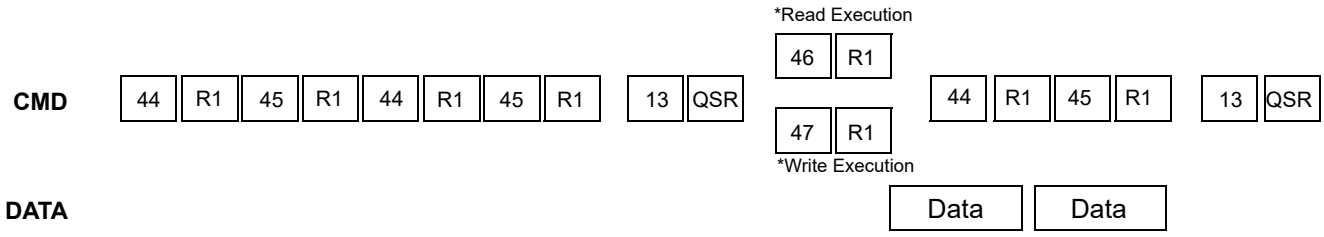
The 32-bit Queue Status Register (QSR) carries the state of tasks in the queue at a specific point in time. The host has read access to this register through device response to SEND_STATUS command (CMD13 with bit[15]=”1”), R1’s argument will be the 32- bit Queue Status Register (QSR). Every bit in the QSR represents the task who’s ID corresponds to the bit index. If bit QSR[i] = “0”, then the queued task with a Task ID i is not ready for execution. The task may be queued and pending, or the Task ID is unused. If bit QSR[i] = “1”, then the queued task with Task ID i is ready for execution.

4.2.3 Send Status : CMD13

CMD13 for reading the Queue Status Register (QSR) by the host. If bit[15] in CMD13’s argument is set to 1, then the device shall send an R1 Response with the QSR instead of the Device Status. There is still legacy CMD13 with R1 response.

4.2.4 Mechanism of CMD Queue Operation

Host issues CMD44 with Task ID number, Sector, Count, Direction, Priority to the device followed by CMD45 and host checks the Queue Status check with CMD13 [15]bits to 1. After that host issues CMD46 for Read or CMD47 for write During CMD queue operation, CMD44/CMD45 is able to be issued at anytime when the CMD line is not in use.



4.2.5 CMD Queue Register Description

Configuration and capability structures shall be added to the EXT_CSD register, as described below.

[Table 14] CMD Queuing Support (EXT_CSD Register : CMDQ_SUPPORT [308])

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved							CMDQ_SUPPORT

This field indicates whether the device supports command queuing or not.
Bit[7-1]: Reserved
Bit[0]: Command queuing support
- **0x0:** CMD Queue function is not supported.
- **0x1:** CMD Queue function is supported.

[Table 15] Command Queue Mode Enable (EXT_CSD Register : CMDQ_MODE_EN [15])

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved							CMDQ_MODE_EN

This field is used by the host enable command queuing.
Bit[7-1]: Reserved
Bit[0]: Command queuing enable
- **0x0:** Queue function is not enabled.
- **0x1:** Queue function is enabled.

[Table 16] CMD Queuing Depth (EXT_CSD Register : CMDQ_DEPTH [307])

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved			N				

This field is used to calculate the depth of the queue supported by the device.
Bit[7-5]: Reserved
Bit[4-0]: N,a parameter used to calculate the Queue Depth of task queue in the device.
- Queue Depth = N+1.

4.3 Enhanced Strobe Mode

This product supports Enhanced Strobe in HS400 mode and refer to the details as described in eMMC5.1 JEDEC standard section 6.15.9.

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4.4 RPMB Throughput Improve

[Table 17] Enhanced RPMB Reliable Write (Related in EXT_CSD Register : WR_REL_PARAM [166])

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved			EN_RPMB_REL_WR	Reserved	EN_REL_WR	Reserved	HS_CTRL_REL

Bit[4]: EN_RPMB_REL_WR(R)
- **0x0:** RPMB transfer size is either 256B (single 512B frame) or 512B (Two 512B frame).
- **0x1:** RPMB transfer size is either 256B (single 512B frame), 512B (Two 512B frame) or 8KB (Thirthy two 512B frames).

4.5 Secure Write Protection

Configuration and capability structures shall be added to the EXT_CSD register and Authenticated Device Configuration Area as described below.

[Table 18] Secure Write Protection (EXT_CSD Register : SECURE_WP_INFO [211])

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved						SECURE_WP_EN_STATUS	SECURE_WP_SUPPORT

Bit[7-2]: Reserved
Bit[1]: SECURE_WP_EN_STATUS(R)
- **0x0:** Legacy Write Protection mode.
- **0x1:** Secure Write Protection mode.

Bit[0]: SECURE_WP_SUPPORT(R)
- **0x0:** Secure Write Protection is NOT supported by this device.
- **0x1:** Secure Write Protection is supported by this device.

[Table 19] Authenticated Device Configuration Area[1] : SECURE_WP_MODE_ENABLE

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved							SECURE_WP_EN

Bit[7-1]: Reserved
Bit[0]: SECURE_WP_EN (R/W/E)
The default value of this field is 0x0.
- **0x0:** Legacy Write Protection mode, i.e., TMP_WRITE_PROTECT[12], PERM_WRITE_PROTECT[13] is updated by CMD27. USER_WP[171], BOOT_WP[173] and BOOT_WP_STATUS[174] are updated by CMD6.
- **0x1:** Secure Write Protection mode. The access to the write protection related EXT_CSD and CSD fields depends on the value of SECURE_WP_MASK bit in SECURE_WP_MODE_CONFIG field.

[Table 20] Authenticated Device Configuration Area[2] : SECURE_WP_MODE_CONFIG

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Reserved							SECURE_WP_MASK

Bit[7-1]: Reserved
Bit[0]: SECURE_WP_MASK (R/W/E_P)
The default value of this field is 0x0.
- **0x0:** Disabling updating WP related EXT_CSD and CSD fields. CMD27 (Program CSD) will generate generic error for setting TMP_WRITE_PROTECT[12], PERM_WRITE_PROTECT[13]. CMD6 for updating USER_WP[171], BOOT_WP[173] and BOOT_WP_STATUS[174] generates SWITCH_ERROR. If a force erase command is issued, the command will fail (Device stays locked) and the LOCK_UNLOCK_FAILED error bit will be set in the status register. If CMD28 or CMD29 is issued, then generic error will be occurred. Power-on Write Protected boot partitions will keep protected mode after power failure, H/W reset assertion and any CMD0 reset. The device keeps the current value of BOOT_WP_STATUS in the EXT_CSD register to be same after power cycle, H/W reset assertion, and any CMD0 reset.

- **0x1:** Enabling updating WP related EXT_CSD and CSD fields. I.e TMP_WRITE_PROTECT[12], PERM_WRITE_PROTECT[13], USER_WP[171], BOOT_WP[173] and BOOT_WP_STATUS[174] are accessed using CMD6, CMD8 and CMD27. If a force erase command is issued and accepted, then ALL THE DEVICE CONTENT WILL BE ERASED including the PWD and PWD_LEN register content and the locked Device will get unlocked. If a force erase command is issued and power-on protected or a permanently-write-protected write protect groups exist on the device, the command will fail (Device stays locked) and the LOCK_UNLOCK_FAILED error bit will be set in the status register. An attempt to force erase on an unlocked Device will fail and LOCK_UNLOCK_FAILED error bit will be set in the status register. Write Protection is applied to the WPG indicated by CMD28 with the WP type indicated by the bit[2] and bit[0] of USER_WP[171]. All temporary WP Groups and power-on Write Protected boot partitions become writable/erasable temporarily which means write protect type is not changed. All power-on and permanent WP Groups in user area will not become writable/erasable temporarily. Those temporarily writable/erasable area will become write protected when this bit is cleared to 0x0 by the host or when there is power failure, H/W reset assertion and any CMD0 reset. The device keeps the current value of BOOT_WP_STATUS in the EXT_CSD register to be same after power cycle, H/W reset assertion, and any CMD0 reset.

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5.0 TECHNICAL NOTES

5.1 S/W Algorithm

5.1.1 Partition Management

The device initially consists of two Boot Partitions and RPMB Partition and User Data Area.

The User Data Area can be divided into four General Purpose Area Partitions and User Data Area partition. Each of the General Purpose Area partitions and a section of User Data Area partition can be configured as enhanced partition. User area density is reduced if enhanced user data area(endhanced partition) is configured, Max Enhanced User Data Area size is defined as (MAX_ENH_SIZE_MULT x HC_WP_GRP_SIZE x HC_ERASE_GRP_SIZE x 512K Bytes) and refer to Table 23 Maximum Enhnaced Partitions Size.

5.1.2 Boot Operation

Device supports not only boot mode but also alternative boot mode. Device supports high speed timing and dual data rate during boot.

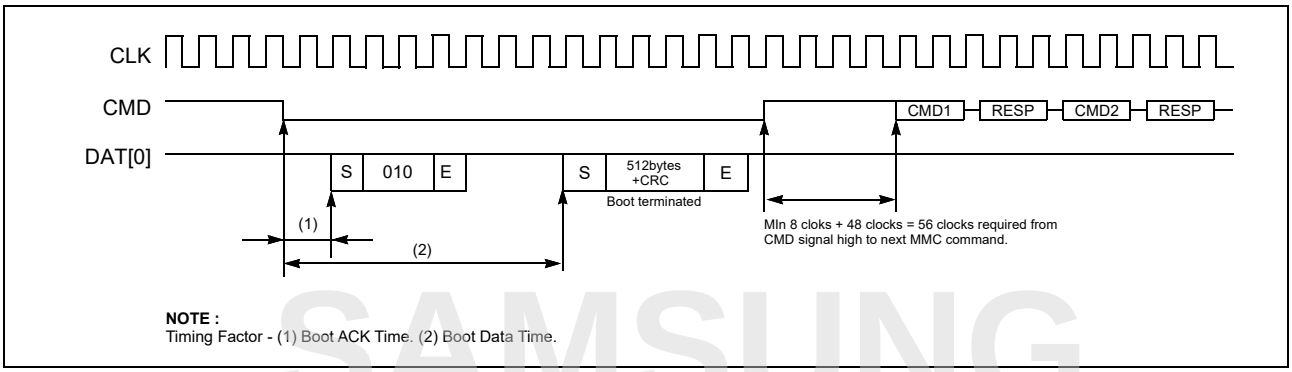


Figure 4. embedded MultiMediaCard State Diagram (Boot Mode)

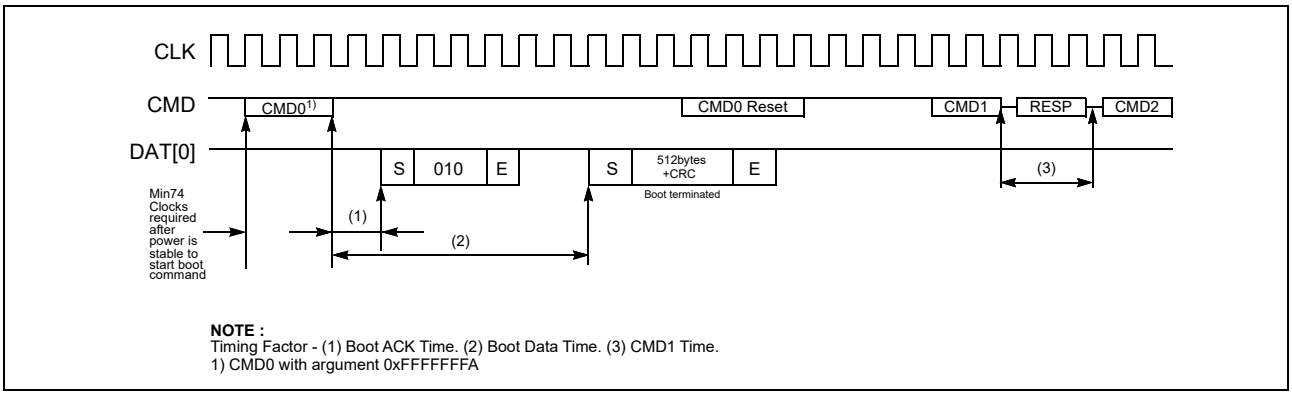


Figure 5. embedded MultiMediaCard State Diagram (Alternative Boot Mode)

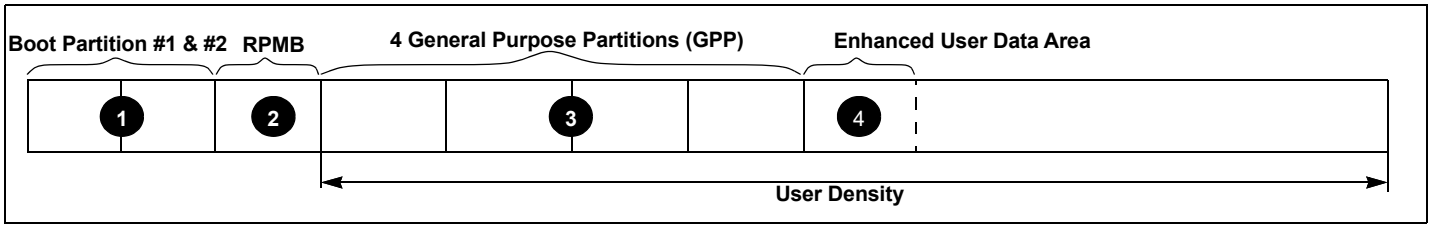
[Table 21] Boot ACK, Boot Data and Initialization Time

Timing Factor	Value
(1) Boot ACK Time	< 50 ms
(2) Boot Data Time	< 100 ms
(3) Initialization Time[1)]	< 3 secs

NOTE :
1) This initialization time includes partition setting, Please refer to INI_TIMEOUT_AP in Chapter 6.4 Extended CSD Register.
Normal initialization time (without partition setting) is completed within 1sec.

5.1.3 User Density

Total User Density depends on device type.



[Table 22] Capacity According to Partition Size

Density	Boot Partition 1	Boot Partition 2	RPMB	Unit
64GB	4,096	4,096	16,384	KB

[Table 23] Maximum Enhanced Partition Size

Density	Enhanced Partition Size (Max.)	Unit
64GB	20,845,690,880	Byte

[Table 24] User Density Size

Density	User Density Size	Unit
64GB	62,537,072,640	Byte

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6.0 REGISTER VALUE

6.1 OCR Register

The 32-bit operation conditions register stores the V_{CCQ} voltage profile of the eMMC. In addition, this register includes a status information bit. This status bit is set if the eMMC power up procedure has been finished. The OCR register shall be implemented by all eMMC.

[Table 25] OCR Register

OCR Bit	V_{CCQ} Voltage Window[1)]	Register Value
[6:0]	Reserved	000 0000b
[7]	1.70 - 1.95V	1b
[14:8]	2.0 - 2.6V	000 0000b
[23:15]	2.7 - 3.6V	1 1111 1111b
[28:24]	Reserved	0 0000b
[30:29]	Access Mode	00b (byte mode), 10b (sector mode) - [*Higher than 2GB only]
[31]	eMMC power up status bit (busy)[2)]	

NOTE :
1) The voltage for internal flash memory(V_{CC}) should be 2.7-3.6V regardless of OCR Register value.
2) This bit is set to LOW if the eMMC has not finished the power up routine.

6.2 CID Register

[Table 26] CID Register

Name	Field	Size (Byte)	CID Slice	CID Value
Manufacturer ID	MID	8	[127:120]	0x15
Reserved		6	[119:114]	0x00
Card/BGA	CBX	2	[113:112]	0x01
OEM / Application ID	OID	8	[111:104]	1)
Product Name	PNM	48	[103:56]	See Product Name Table
Product Revision	PRV	8	[55:48]	2)
Product Serial Number	PSN	32	[47:16]	3)
Manufacturing Date	MDT	8	[15:8]	4)
CRC7 Checksum	CRC	7	[7:1]	5)
Not Used, Always '1'		1	[0:0]	0x01

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NOTE :
1),4),5) description are same as eMMC JEDEC standard.
2) PRV is composed of the revision count of controller and the revision count of F/W patch.
3) A 32 bits unsigned binary integer. (Random Number).

6.2.1 Product Name Table (In CID Register)

[Table 27] Product Name Table

Density	Product ID	Product Name in CID Register (PNM)
64GB	KLMCG1RCTE-B041	0x435254453432

6.3 CSD Register

The Card-Specific Data register provides information on how to access the eMMC contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register (entries marked by W or E, see below) can be changed by CMD27.

The type of the entries in the table below is coded as follows:

- **R:** Read only.
- **W:** One time programmable and not readable.
- **R/W:** One time programmable and readable.
- **W/E:** Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and not readable.
- **R/W/E:** Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and readable.
- **R/W/C_P:** Writable after value cleared by power failure and HW/ rest assertion (the value not cleared by CMD0 reset) and readable.
- **R/W/E_P:** Multiple writable with value reset after power failure, H/W reset assertion and any CMD0 reset and readable.
- **W/E_P:** Multiple writable with value reset after power failure, H/W reset assertion and any CMD0 reset and not readable.

[Table 28] CSD Register

Name	Field	Size (Byte)	Cell Type	CSD Slice	CSD Value
CSD Structure	CSD_STRUCTURE	2	R	[127:126]	0x03
System Specification Version	SPEC_VERS	4	R	[125:122]	0x04
Reserved		2	R	[121:120]	0x00
Data Read Access-Time 1	TAAC	8	R	[119:112]	0x27
Data Read Access-Time 2 in CLK Cycles (NSAC*100)	NSAC	8	R	[111:104]	0x01
Max. Bus Clock Frequency	TRAN_SPEED	8	R	[103:96]	0x32
Device Command Classes	CCC	12	R	[95:84]	0xF5
Max. Read Data Block Length	READ_BL_LEN	4	R	[83:80]	0x09
Partial Blocks for Read Allowed	READ_BL_PARTIAL	1	R	[79:79]	0x00
Write Block Misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]	0x00
Read Block Misalignment	READ_BLK_MISALIGN	1	R	[77:77]	0x00
DSR Implemented	DSR_IMP	1	R	[76:76]	0x00
Reserved		2	R	[75:74]	0x00
Device Size	C_SIZE	12	R	[73:62]	0xFFF
Max. Read Current @ VDD Min	VDD_R_CURR_MIN	3	R	[61:59]	0x06
Max. Read Current @ VDD Max	VDD_R_CURR_MAX	3	R	[58:56]	0x06
Max. Write Current @ VDD Min	VDD_W_CURR_MIN	3	R	[55:53]	0x06
Max. Write Current @ VDD Max	VDD_W_CURR_MAX	3	R	[52:50]	0x06
Device Size Multiplier	C_SIZE_MULT	3	R	[49:47]	0x07
Erase Group Size	ERASE_GRP_SIZE	5	R	[46:42]	0x1F
Erase Group Size Multiplier	ERASE_GRP_MULT	5	R	[41:37]	0x1F
Write Protect Group Size	WP_GRP_SIZE	5	R	[36:32]	0x0F
Write Protect Group Enable	WP_GRP_ENABLE	1	R	[31:31]	0x01
Manufacturer Default ECC	DEFAULT_ECC	2	R	[30:29]	0x00
Write Speed Factor	R2W_FACTOR	3	R	[28:26]	0x03
Max. Write Data Block Length	WRITE_BL_LEN	4	R	[25:22]	0x09
Partial Blocks for Write Allowed	WRITE_BL_PARTIAL	1	R	[21:21]	0x00
Reserved		4	R	[20:17]	0x00
Content Protection Application	CONTENT_PROT_APP	1	R	[16:16]	0x00
File Format Group	FILE_FORMAT_GRP	1	R/W	[15:15]	0x00
Copy Flag (OTP)	COPY	1	R/W	[14:14]	0x01
Permanent Write Protection	PERM_WRITE_PROTECT	1	R/W	[13:13]	0x00
Temporary Write Protection	TMP_WRITE_PROTECT	1	R/W/E	[12:12]	0x00
File Format	FILE_FORMAT	2	R/W	[11:10]	0x00
ECC Code	ECC	2	R/W/E	[9:8]	0x00
CRC	CRC	7	R/W/E	[7:1]	0x06
Not used, Always '1'		1		[0:0]	0x01

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6.4 Extended CSD Register

The Extended CSD register defines the eMMC properties and selected modes. It is 512 bytes long.
The most significant 320 bytes are the Properties segment, which defines the eMMC capabilities and cannot be modified by the host. The lower 192 bytes are the Modes segment, which defines the configuration the eMMC is working in. These modes can be changed by the host by means of the SWITCH command.

The type of the entries in the table below is coded as follows:

- **R:** Read only.
- **W:** One time programmable and not readable.
- **R/W:** One time programmable and readable.
- **W/E:** Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and not readable.
- **R/W/E:** Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and readable.
- **R/W/C_P:** Writable after value cleared by power failure and HW/ rest assertion (the value not cleared by CMD0 reset) and readable.
- **R/W/E_P:** Multiple writable with value reset after power failure, H/W reset assertion and any CMD0 reset and readable.
- **W/E_P:** Multiple writable with value reset after power failure, H/W reset assertion and any CMD0 reset and not readable.

[Table 29] Extended CSD Register

Name	Field	Size (Byte)	Cell Type	CSD Slice	CSD Value
Properties Segment					
Reserved		6		[511:506]	0x00
Extended Security Commands Error	EXT_SECURITY_ERR	1	R	[505]	0x00
Supported Command Sets	S_CMD_SET	1	R	[504]	0x01
HPI Features	HPI_FEATURES	1	R	[503]	0x01
Background Operations Support	BKOPS_SUPPORT	1	R	[502]	0x01
Max Packed Read Commands	MAX_PACKED_READS	1	R	[501]	0x3F
Max Packed Write Commands	MAX_PACKED_WRITES	1	R	[500]	0x3F
Data Tag Support	DATA_TAG_SUPPORT	1	R	[499]	0x01
Tag Unit Size	TAG_UNIT_SIZE	1	R	[498]	0x02
Tag Resources Size	TAG_RES_SIZE	1	R	[497]	0x00
Context Management Capabilities	CONTEXT_CAPABILITIES	1	R	[496]	0x05
Large Unit Size	LARGE_UNIT_SIZE_M1	1	R	[495]	0x07
Extended Partitions Attribute Support	EXT_SUPPORT	1	R	[494]	0x03
Supported Modes	SUPPORTED_MODES	1	R	[493]	0x03
FFU Features	FFU_FEATURES	1	R	[492]	0x00
Operation Codes Timeout	OPERATION_CODE_TIMEOUT	1	R	[491]	0x00
FFU Argument	FFU_ARG	4	R	[490:487]	0x000081C7
Barrier Support	BARRIER_SUPPORT	1	R	[486]	0x01
Reserved		177		[485:309]	0x00
CMD Queuing Support	CMDQ_SUPPORT	1	R	[308]	0x01
CMD Queuing Depth	CMDQ_DEPTH	1	R	[307]	0x0F
Reserved		1		[306]	0x00
Number of FW Sectors Correctly Programmed	NUMBER_OF_FW_SECTORS_CORRECTLY_PROGRAMMED	4	R	[305:302]	0x00000000
Vendor Proprietary Health Report	VENDOR_PROPRIETARY_HEALTH_REPORT	32	R	[301:270]	0x00
Device Life Time Estimation Type B	DEVICE_LIFE_TIME_EST_TYP_B	1	R	[269]	0x05
Device Life Time Estimation Type A	DEVICE_LIFE_TIME_EST_TYP_A	1	R	[268]	0x01
Pre EOL Information	PRE_EOL_INFO	1	R	[267]	0x01
Optimal Read Size	OPTIMAL_READ_SIZE	1	R	[266]	0x00
Optimal Write Size	OPTIMAL_WRITE_SIZE	1	R	[265]	0x18
Optimal Trim Unit Size	OPTIMAL_TRIM_UNIT_SIZE	1	R	[264]	0x01
Device Version	DEVICE_VERSION	2	R	[263:262]	0x00
Firmware Version	FIRMWARE_VERSION	8	R	[261:254]	FW Version

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[Table 29] Extended CSD Register

Name	Field	Size (Byte)	Cell Type	CSD Slice	CSD Value
Power Class for 200MHz, DDR at V_{CC}=3.6V	PWR_CL_DDR_200_360	1	R	[253]	0x00
Cache Size	CACHE_SIZE	4	R	[252:249]	0x10000
Generic CMD6 Timeout	GENERIC_CMD6_TIME	1	R	[248]	0x0A
Power Off Notification (Long) Timeout	POWER_OFF_LONG_TIME	1	R	[247]	0x3C
Background Operations Status	BKOPS_STATUS	1	R	[246]	0x00
Number of Correctly Programmed Sectors	CORRECTLY_PRG_SECTORS_NUM	4	R	[245:242]	0x00000000
1st Initialization Time after Partitioning	INI_TIMEOUT_AP	1	R	[241]	0x1E
Cache Flush Policy	CACHE_FLUSH_POLICY	1	R	[240]	0x01
Power Class for 52MHz, DDR at 3.6V	PWR_CL_DDR_52_360	1	R	[239]	0x00
Power Class for 52MHz, DDR at 1.95V	PWR_CL_DDR_52_195	1	R	[238]	0x00
Power Class for 200MHz at V_{CCQ}=1.95V, V_{CC}=3.6V	PWR_CL_200_360	1	R	[237]	0x00
Power Class for 200MHz, at V_{CCQ}=1.3V, V_{CC}=3.6V	PWR_CL_200_195	1	R	[236]	0x00
Minimum Write Performance for 8bit at 52MHz in DDR Mode	MIN_PERF_DDR_W_8_52	1	R	[235]	0x00
Minimum Read Performance for 8bit at 52MHz in DDR Mode	MIN_PERF_DDR_R_8_52	1	R	[234]	0x00
Reserved		1		[233]	0x00
Trim Multiplier	TRIM_MULT	1	R	[232]	0x02
Secure Feature Support	SEC_FEATURE_SUPPORT	1	R	[231]	0x55
Secure Erase Multiplier	SEC_ERASE_MULT	1	R	[230]	0x1B
Secure Trim Multiplier	SEC_TRIM_MULT	1	R	[229]	0x11
Boot Information	BOOT_INFO	1	R	[228]	0x07
Reserved		1		[227]	0x00
Boot Partition Size	BOOT_SIZE_MULT	1	R	[226]	0x20
Access Size	ACC_SIZE	1	R	[225]	0x07
High-Capacity Erase Unit Size	HC_ERASE_GRP_SIZE	1	R	[224]	0x01
High-Capacity Erase Timeout	ERASE_TIMEOUT_MULT	1	R	[223]	0x01
Reliable Write Sector Count	REL_WR_SEC_C	1	R	[222]	0x01
High-Capacity Write Protect Group Size	HC_WP_GRP_SIZE	1	R	[221]	0x10
Sleep Current (V_{CC})	S_C_VCC	1	R	[220]	0x07
Sleep Current (V_{CCQ})	S_C_VCCQ	1	R	[219]	0x07
Production State Awareness Timeout	PRODUCTION_STATE_AWARENESS_-TIMEOUT	1	R	[218]	0x00
Sleep / Awake Timeout	S_A_TIMEOUT	1	R	[217]	0x13
Sleep Notification Timeout	SLEEP_NOTIFICATION_TIME	1	R	[216]	0x0C
Sector Count	SEC_COUNT	4	R	[215:212]	0x747C000
Secure Write Protect Information	SECURE_WP_INFO	1	R	[211]	0x01
Minimum Write Performance for 8bit at 52MHz	MIN_PERF_W_8_52	1	R	[210]	0x00
Minimum Read Performance for 8bit at 52MHz	MIN_PERF_R_8_52	1	R	[209]	0x00
Minimum Write Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_W_8_26_4_52	1	R	[208]	0x00
Minimum Read Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_R_8_26_4_52	1	R	[207]	0x00
Minimum Write Performance for 4bit at 26MHz	MIN_PERF_W_4_26	1	R	[206]	0x00
Minimum Read Performance for 4bit at 26MHz	MIN_PERF_R_4_26	1	R	[205]	0x00
Reserved		1		[204]	0x00
Power Class for 26MHz at 3.6V 1 R	PWR_CL_26_360	1	R	[203]	0x00

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[Table 29] Extended CSD Register

Name	Field	Size (Byte)	Cell Type	CSD Slice	CSD Value
Power Class for 52MHz at 3.6V 1 R	PWR_CL_52_360	1	R	[202]	0x00
Power Class for 26MHz at 1.95V 1 R	PWR_CL_26_195	1	R	[201]	0x00
Power Class for 52MHz at 1.95V 1 R	PWR_CL_52_195	1	R	[200]	0x00
Partition Switching Timing	PARTITION_SWITCH_TIME	1	R	[199]	0x05
Out-of-Interrupt Busy Timing	OUT_OF_INTERRUPT_TIME	1	R	[198]	0x0A
I/O Driver Strength	DRIVER_STRENGTH	1	R	[197]	0x1F
Device Type	DEVICE_TYPE	1	R	[196]	0x57
Reserved		1		[195]	0x00
CSD Structure	CSD_STRUCTURE	1	R	[194]	0x02
Reserved		1		[193]	0x00
Extended CSD Revision	EXT_CSD_REV	1	R	[192]	0x08
Modes Segment					
Command Set	CMD_SET	1	R/W/E_P	[191]	0x00
Reserved		1		[190]	0x00
Command Set Revision	CMD_SET_REV	1	R	[189]	0x00
Reserved		1		[188]	0x00
Power Class	POWER_CLASS	1	R/W/E_P	[187]	0x00
Reserved		1		[186]	0x00
High-Speed Interface Timing	HS_TIMING	1	R/W/E_P	[185]	0x01
Strobe Support	STROBE_SUPPORT	1	R	[184]	0x01
Bus Width Mode	BUS_WIDTH	1	W/E_P	[183]	0x00
Reserved		1		[182]	0x00
Erased Memory Content	ERASED_MEM_CONT	1	R	[181]	0x00
Reserved		1		[180]	0x00
Partition Configuration	PARTITION_CONFIG	1	R/W/E & R/W/E_P	[179]	0x00
Boot Config Protection	BOOT_CONFIG_PROT	1	R/W & R/W/C_P	[178]	0x00
Boot Bus Conditions	BOOT_BUS_CONDITIONS	1	R/W/E	[177]	0x00
Reserved		1		[176]	0x00
High-Density Erase Group Definition	ERASE_GROUP_DEF	1	R/W/E_P	[175]	0x00
Boot Write Protection Status Registers	BOOT_WP_STATUS	1	R	[174]	0x00
Boot Area Write Protection Register	BOOT_WP	1	R/W & R/W/C_P	[173]	0x00
Reserved		1		[172]	0x00
User Area Write Protection Register	USER_WP	1	R/W, R/W/C_P &R/W/E_P	[171]	0x00
Reserved		1		[170]	0x00
FW Configuration	FW_CONFIG	1	R/W	[169]	0x00
RPMB Size	RPMB_SIZE_MULT	1	R	[168]	0x80
Write Reliability Setting Register	WR_REL_SET	1	R/W	[167]	0x1F
Write Reliability Parameter Register	WR_REL_PARAM	1	R	[166]	0x14
Start Sanitize Operation	SANITIZE_START	1	W/E_P	[165]	0x00
Manually Start Background Operations	BKOPS_START	1	W/E_P	[164]	0x00
Enable Background Operations Handshake	BKOPS_EN	1	R/W&R/W/E	[163]	0x00
H/W Reset Function	RST_n_FUNCTION	1	R/W	[162]	0x00
HPI Management	HPI_MGMT	1	R/W/E_P	[161]	0x00
Partitioning Support	PARTITIONING_SUPPORT	1	R	[160]	0x07

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[Table 29] Extended CSD Register

Name	Field	Size (Byte)	Cell Type	CSD Slice	CSD Value
Max Enhanced Area Size	MAX_ENH_SIZE_MULT	3	R	[159:157]	0x9B5
Partitions Attribute	PARTITIONS_ATTRIBUTE	1	R/W	[156]	0x00
Partitioning Setting	PARTITION_SETTING_ COMPLETED	1	R/W	[155]	0x00
General Purpose Partition Size	GP_SIZE_MULT	12	R/W	[154:143]	0x00
Enhanced User Data Area Size	ENH_SIZE_MULT	3	R/W	[142:140]	0x00
Enhanced User Data Start Address	ENH_START_ADDR	4	R/W	[139:136]	0x00
Reserved		1		[135]	0x00
Bad Block Management Mode	SEC_BAD_BLK_MGMNT	1	R/W	[134]	0x00
Production State Awareness	PRODUCTION_STATE_AWARENESS	1	R/W/E	[133]	0x00
Package Case Temperature is Controlled	TCASE_SUPPORT	1	W/E_P	[132]	0x00
Periodic Wake-Up	PERIODIC_WAKEUP	1	R/W/E	[131]	0x00
Program CID / CSD in DDR Mode Support	PROGRAM_CID_CSD_DDR_SUPPORT	1	R	[130]	0x01
Reserved		2		[129:128]	0x00
Vendor Specific Fields	VENDOR_SPECIFIC_FIELD	64	Vendor Specific	[127:64]	Vendor Specific
Native Sector Size	NATIVE_SECTOR_SIZE	1	R	[63]	0x00
Sector Size Emulation	USE_NATIVE_SECTOR	1	R/W	[62]	0x00
Sector Size	DATA_SECTOR_SIZE	1	R	[61]	0x00
1st Initialization after Disabling Sector Size Emulation	INI_TIMEOUT_EMU	1	R	[60]	0x00
Class 6 Commands Control	CLASS_6_CTRL	1	R/W/E_P	[59]	0x00
Number of Addressed Group to be Released	DYNCAP_NEEDED	1	R	[58]	0x00
Exception Events Control	EXCEPTION_EVENTS_CTRL	2	R/W/E_P	[57:56]	0x00
Exception Events Status	EXCEPTION_EVENTS_STATUS	2	R	[55:54]	0x00
Extended Partitions Attribute	EXT_PARTITIONS_ATTRIBUTE	2	R/W	[53:52]	0x00
Context Configuration	CONTEXT_CONF	15	R/W/E_P	[51:37]	0x00
Packed Command Status	PACKED_COMMAND_STATUS	1	R	[36]	0x00
Packed Command Failure Index	PACKED_FAILURE_INDEX	1	R	[35]	0x00
Power Off Notification	POWER_OFF_NOTIFICATION	1	R/W/E_P	[34]	0x00
Control to Turn the Cache On / Off	CACHE_CTRL	1	R/W/E_P	[33]	0x00
Flushing of the Cache	FLUSH_CACHE	1	W/E_P	[32]	0x00
Control to Turn the Barrier On / Off	BARRIER_CTRL	1	R/W	[31]	0x00
Mode Config	MODE_CONFIG	1	R/W/E_P	[30]	0x00
Mode Operation Codes	MODE_OPERATION_CODES	1	W/E_P	[29]	0x00
Reserved		2		[28:27]	0x00
FFU Status	FFU_STATUS	1	R	[26]	0x00
Pre Loading Data Size	PRE_LOADING_DATA_SIZE	4	R/W/E_P	[25:22]	0x00
Max Pre Loading Data Size	MAX_PRE_LOADING_DATA_SIZE	4	R	[21:18]	0x00
Product State Awareness Enablement	PRODUCT_STATE_AWARENESS_ENABLEMENT	1	R/W/E & R	[17]	0x00
Secure Removal Type	SECURE_REMOVAL_TYPE	1	R/W & R	[16]	0x39
Command Queue Mode Enable	CMDQ_MODE_EN	1	R/W/E_P	[15]	0x00
Reserved		15		[14:0]	0x00

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7.0 DC PARAMETER

7.1 Power Consumption

7.1.1 Active Power Consumption During Operation

[Table 30] Active Power Consumption During Operation

Density	V_{CC}	V_{CCQ}	Unit
64GB	150	200	mA

NOTE :
Power Measurement conditions: Bus configuration =x8 @HS400.
The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

7.1.2 Standby Power Consumption in Auto Power Saving Mode and Standby Mode

[Table 31] Standby Power Consumption in Auto Power Saving Mode and Standby Mode

Density	V_{CC}	V_{CCQ}	Unit
64GB	80	200	uA

NOTE :
Power Measurement conditions: Bus configuration =x8, No CLK.
Typical value is measured at V_{CC}=3.3V, Ta=25°C. Not 100% tested.

7.1.3 Sleep Power Consumption in Sleep Mode

[Table 32] Sleep Power Consumption in Sleep Mode

Density	V_{CC}	V_{CCQ}	Unit
64GB	0[1)]	200	uA

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NOTE :
Power Measurement conditions: Bus configuration =x8, No CLK.
1) In auto power saving mode, V_{CC} power supply shall not be turned off. However in sleep mode V_{CC} power is turned off.

8.0 AC PARAMETER

8.1 Timing Parameter

[Table 33] Timing Parameter

Timing Parameter		Value (Max.)	Unit
Initialization Time (tINIT)	Normal[1)]	1	s
	After Partition Setting[2)]	3	s
Read Timeout		100	ms
Write Timeout		350	ms
Erase Timeout		20	ms
Force Erase Timeout		3	min
Secure Erase Timeout		8	s
Secure Trim Step1 Timeout		5	s
Secure Trim Step2 Timeout		3	s
Trim Timeout		300	ms
Partition Switching Timeout (after Init)		10[3)]	ms
Power Off Notification (Short) Timeout		100	ms
Power Off Notification (Long) Timeout		600	ms

NOTE :
Be advised Timeout Values specified in Table above are for testing purposes under Samsung test pattern only and actual timeout situations may vary.
EXCEPTION_EVENT may occur and the actual timeout values may vary due to user environment.
1) Normal Initialization Time without partition setting.
2) Initialization Time after partition setting, refer to INI_TIMEOUT_AP in Chapter 6.4 EXT_CSD register.
3) During SLC to TLC migration max value could be up to 75ms.

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8.2 Previous Bus Timing Parameters for DDR52 and HS200 Mode are defined by JEDEC Standard

8.3 Bus Timing Specification in HS400 Mode

8.3.1 HS400 Device Input Timing

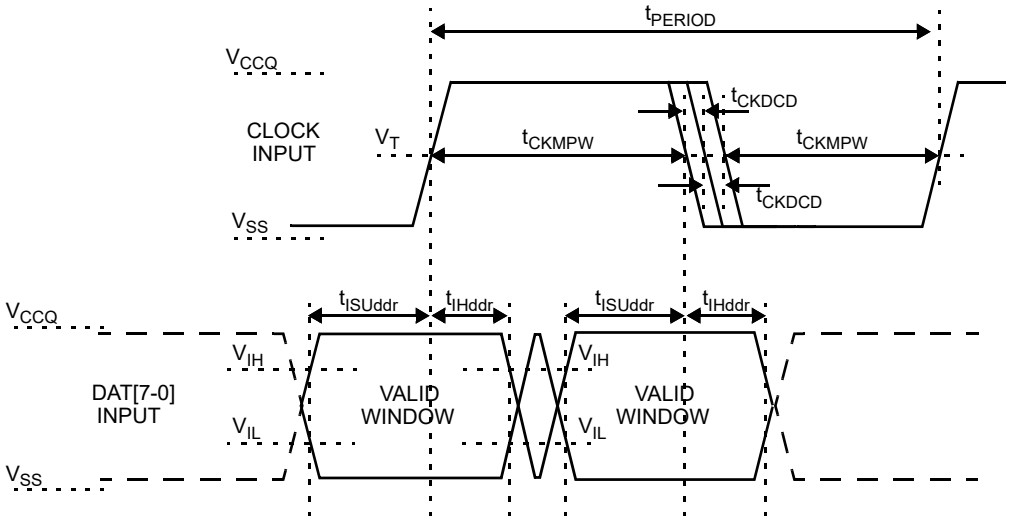


Figure 6. HS400 Device Input Timing

NOTE :
t_{ISU} and t_{IH} are measured at V_{IL}(max) and V_{IH}(min).
V_{IH} denotes V_{IH}(min) and V_{IL} denotes V_{IL}(max).

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[Table 34] HS400 Device Input Timing

Parameter	Symbol	Min	Max	Unit
Input CLK				
Cycle Time Data Transfer Mode	t_{PERIOD}	5		ns
Slew Rate	SR	1.125		V/ns
Duty Cycle Distortion	t_{CKDCD}	0.0	0.3	ns
Minimum Pulse Width	t_{CKMPW}	2.2		ns
Input Dat (Referenced to CLK)				
Input Set-Up Time	t_{ISUddr}	0.4		ns
Input Hold Time	t_{IHddr}	0.4		ns
Slew Rate	SR	1.125		V/ns

8.3.2 HS400 Device Output Timing

Data Strobe is used to read data (data read and CRC status response read) in HS400 mode.
The device output value of Data Strobe is “High-Z” when the device is not in outputting data (data read, CRC status response).
Data Strobe is toggled only during data read period.

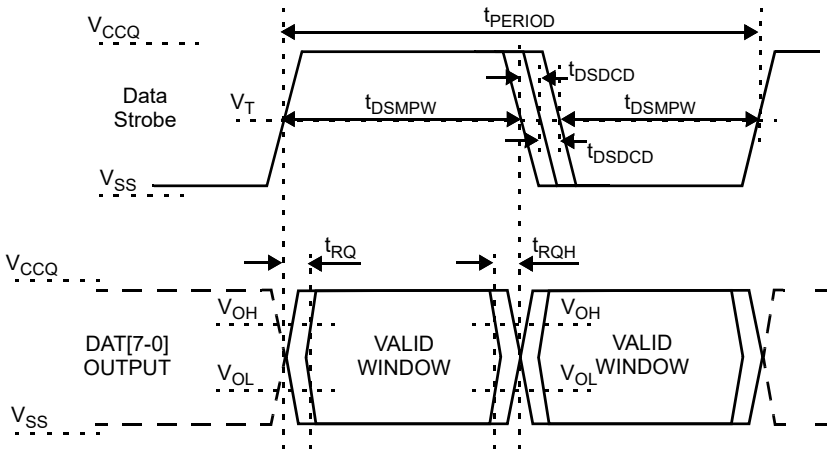


Figure 7. HS400 Device Output Timing

NOTE :
V_{OH} denotes V_{OH}(min) and V_{OL} denotes V_{OL}(max).

[Table 35] HS400 Device Output Timing

Parameter	Symbol	Min	Max	Unit
Data Strobe				
Cycle Time Data Transfer Mode	t_{PERIOD}	5		ns
Slew Rate	SR	1.125		V/ns
Duty Cycle Distortion	t_{DSDCD}	0.0	0.2	ns
Minimum Pulse Width	t_{DSMPW}	2.0		ns
Read Pre-Amble	t_{RPRE}	0.4		t_{PERIOD}
Read Post-Amble	t_{RPST}	0.4		t_{PERIOD}
Output DAT (Referenced to Data Strobe)				
Output Skew	t_{RQ}		0.4	ns
Output Hold Skew	t_{RQH}		0.4	ns
Slew Rate	SR	1.125		V/ns

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8.4 Bus Signal Line Load

The total capacitance C_L of each line of the eMMC bus is the sum of the bus master capacitance C_{HOST}, the bus capacitance C_{BUS} itself and the capacitance C_{DEVICE} of the eMMC connected to this line:

$$C_L = C_{HOST} + C_{BUS} + C_{DEVICE}$$

The sum of the host and bus capacitances should be under 20pF.

[Table 36] Bus Signal Line Load

Parameter	Symbol	Min	Max	Unit	Remark
Pull-Up Resistance for CMD	R_{CMD}	4.7	100	KOhm	to prevent bus floating
Pull-Up Resistance for DAT0-DAT7	R_{DAT}	10	100	KOhm	to prevent bus floating
Internal Pull Up Resistance DAT1-DAT7	R_{int}	10	150	KOhm	to prevent unconnected lines floating
Single Device Capacitance	C_{DEVICE}		12	pF	
Maximum Signal Line Inductance			16	nH	f_{PP} <= 52 MHz

[Table 37] Capacitance and Resistance for HS400 Mode

Parameter	Symbol	Min	Max	Unit	Remark
Bus Signal Line Capacitance	C_L		13	pF	Single Device
Single Device Capacitance	C_{DEVICE}		6	pF	
Pull-Down Resistance for Data Strobe	$R_{Data\ Strobe}$	10	100	KOhm	

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8.5 Bus Signal Levels

As the bus can be supplied with a variable supply voltage, all signal levels are related to the supply voltage.

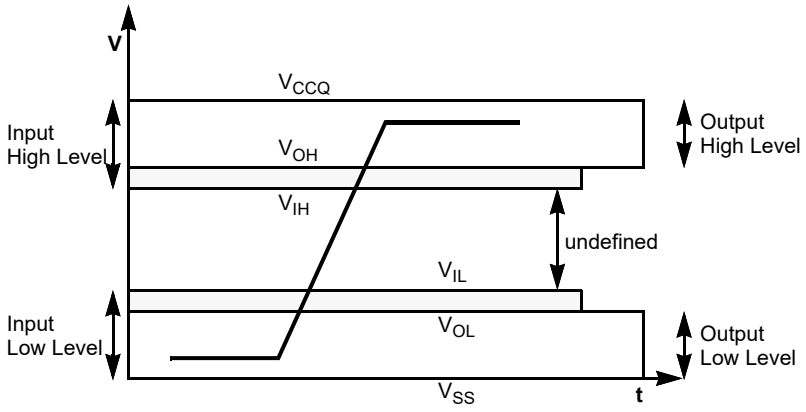


Figure 8. Bus Signal Levels

8.5.1 Open-Drain Mode Bus Signal Level

[Table 38] Open-Drain Bus Signal Level

Parameter	Symbol	Min	Max	Unit	Condition
Output High Voltage	V_{OH}	V_{CCQ} - 0.2		V	1)
Output Low Voltage	V_{OL}		0.3	V	I_{OL} = 2 mA

NOTE :
1) Because V_{OH} depends on external resistance value (including outside the package), this value does not apply as device specification.
Host is responsible to choose the external pull-up and open drain resistance value to meet V_{OH} Min value.

8.5.2 Push-Pull Mode Bus Signal Level eMMC

The device input and output voltages shall be within the following specified ranges for any V_{CCQ} of the allowed voltage range.

[Table 39] Push-Pull Signal Level—High-Voltage eMMC

Parameter	Symbol	Min	Max	Unit	Condition
Output High Voltage	V_{OH}	0.75*V_{CCQ}		V	I_{OH} = -100 uA@V_{CCQ} min
Output Low Voltage	V_{OL}		0.125*V_{CCQ}	V	I_{OL} = 100 uA@V_{CCQ} min
Input High Voltage	V_{IH}	0.625*V_{CCQ}	V_{CCQ} + 0.3	V	
Input Low Voltage	V_{IL}	V_{SS} - 0.3	0.25*V_{CCQ}	V	

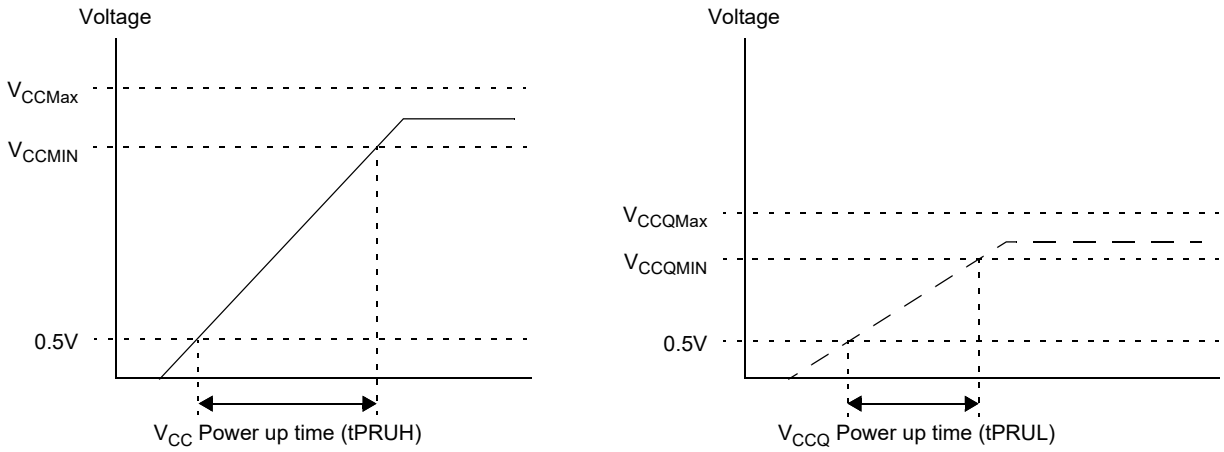
[Table 40] Push-Pull Signal Level—1.70 - 1.95 V_{CCQ} Voltage Range

Parameter	Symbol	Min	Max	Unit	Condition
Output High Voltage	V_{OH}	V_{CCQ} - 0.45V		V	I_{OH} = -2mA
Output Low Voltage	V_{OL}		0.45V	V	I_{OL} = 2mA
Input High Voltage	V_{IH}	0.65*V_{CCQ} 1)	V_{CCQ} + 0.3	V	
Input Low Voltage	V_{IL}	V_{SS} - 0.3	0.35*V_{CCQ} 2)	V	

NOTE :
1) 0.7*V_{CCQ} for MMC4.3 and older revisions.
2) 0.3*V_{CCQ} for MMC4.3 and older revisions.

8.5.3 Power Up Sequence

An eMMC bus power-up is handled locally in each device and in the bus master. When power-up is initiated, either V_{CC} or V_{CCQ} can be ramped up first, or both can be ramped up simultaneously. For more detailed information, refer to eMMC5.1 JEDEC standard.



NOTE :
V_{CCMIN}, V_{CCQMIN} and tPRUH, tPRUL timing shown in Table 3.

Figure 9. Power Up Timings

8.5.4 Power Cycling

The master can execute any sequence of V_{CC} and V_{CCQ} power-up/power-down. However, the master must not issue any commands until V_{CC} and V_{CCQ} are stable within each operating voltage range. After the slave enters sleep mode, the master can power-down V_{CC} to reduce power consumption. It is necessary for the slave to be ramped up to V_{CC} before the host issues CMD5 (SLEEP_AWAKE) to wake the slave unit.
Once V_{CC} or V_{CCQ} are drops the minimum guaranteed voltage, shall be stayed under 0.5V for at least 1ms before powered up again.
If V_{CC} or V_{CCQ} are below 0.5V for longer than 1 ms, the slave shall always return to the pre-idle state, and perform the appropriate boot behavior, as appropriate. The slave will behaves as in a standard power-up condition once the voltages have returned to their functional ranges.
For more detailed information, refer to eMMC5.1 JEDEC standard.

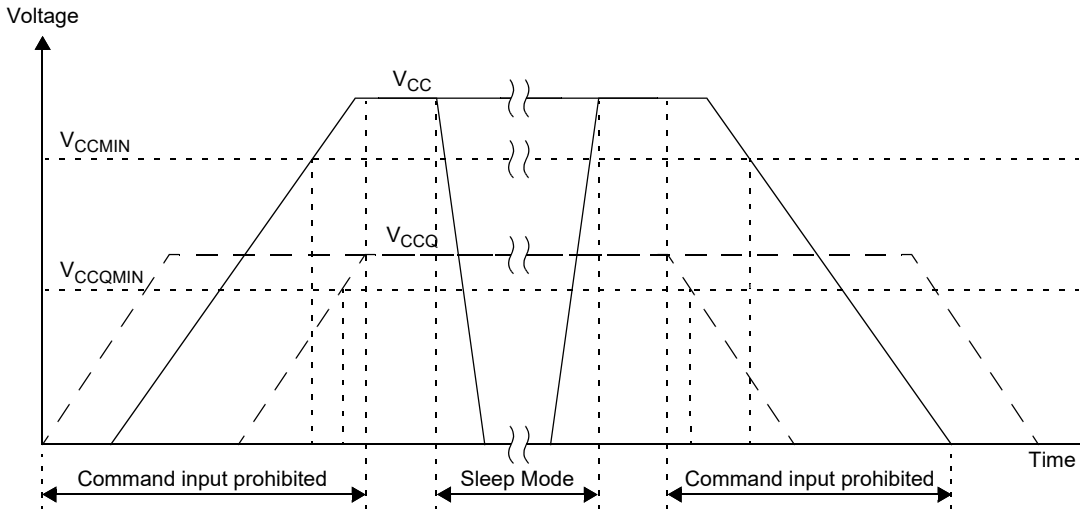


Figure 10. Power Cycling